1.8 V high output drive configurable registered buffer for DDR2 RDIMM applications

Rev. 01 — 22 April 2005

Product data sheet

1. General description

The SSTUH32864 is a 25-bit 1 : 1 or 14-bit 1 : 2 configurable registered buffer designed for 1.7 V to 1.9 V V_{DD} operation.

All clock and data inputs are compatible with the JEDEC standard for SSTL_18. The control inputs are LVCMOS. All outputs are 1.8 V CMOS drivers that have been optimized to drive the DDR2 DIMM load.

The SSTUH32864 operates from a differential clock (CK and \overline{CK}). Data are registered at the crossing of CK going HIGH, and \overline{CK} going LOW.

The C0 input controls the pinout configuration of the 1 : 2 pinout from A configuration (when LOW) to B configuration (when HIGH). The C1 input controls the pinout configuration from 25-bit 1 : 1 (when LOW) to 14-bit 1 : 2 (when HIGH).

The device supports low-power standby operation. When the reset input (RESET) is LOW, the differential input receivers are disabled, and un-driven (floating) data, clock and reference voltage (VREF) inputs are allowed. In addition, when RESET is LOW all registers are reset, and all outputs are forced LOW. The LVCMOS RESET and Cn inputs must always be held at a valid logic HIGH or LOW level.

To ensure defined outputs from the register before a stable clock has been supplied, RESET must be held in the LOW state during power-up.

In the DDR2 RDIMM application, \overrightarrow{RESET} is specified to be completely asynchronous with respect to CK and \overrightarrow{CK} . Therefore, no timing relationship can be guaranteed between the two. When entering reset, the register will be cleared and the data outputs will be driven LOW quickly, relative to the time to disable the differential input receivers. However, when coming out of reset, the register will become active quickly, relative to the time to enable the differential input receivers. As long as the data inputs are LOW, and the clock is stable during the time from the LOW-to-HIGH transition of \overrightarrow{RESET} until the input receivers are fully enabled, the design of the SSTUH32864 must ensure that the outputs will remain LOW, thus ensuring no glitches on the output.

The device monitors both $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ inputs and will gate the Qn outputs from changing states when both $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ inputs are HIGH. If either $\overline{\text{DCS}}$ or $\overline{\text{CSR}}$ input is LOW, the Qn outputs will function normally. The RESET input has priority over the $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control and will force the outputs LOW. If the $\overline{\text{DCS}}$ -control functionality is not desired, then the $\overline{\text{CSR}}$ input can be hardwired to ground, in which case the setup time requirement for $\overline{\text{DCS}}$ would be the same as for the other Dn data inputs.

The SSTUH32864 is available in a 96-ball, low profile fine-pitch ball grid array (LFBGA96) package.



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The SSTUH32864 is identical to SSTU32864 in function and performance, with higher-drive outputs optimized to drive heavy load nets (such as stacked DRAMs) while maintaining speed and signal integrity.

2. Features

- Configurable register supporting DDR2 Registered DIMM applications
- Higher output drive strength version of SSTU32864 optimized for high-capacitive load nets
- Configurable to 25-bit 1 : 1 mode or 14-bit 1 : 2 mode
- Controlled output impedance drivers enable optimal signal integrity and speed
- Exceeds JESD82-7 speed performance (1.8 ns max. single-bit switching propagation delay; 2.0 ns max. mass-switching)
- Supports up to 450 MHz clock frequency of operation
- Optimized pinout for high-density DDR2 module design
- Chip-selects minimize power consumption by gating data outputs from changing state
- Supports SSTL_18 data inputs
- Differential clock (CK and CK) inputs
- Supports LVCMOS switching levels on the control and RESET inputs
- Single 1.8 V supply operation
- Available in 96-ball, 13.5 × 5.5 mm, 0.8 mm ball pitch LFBGA package

3. Ordering information

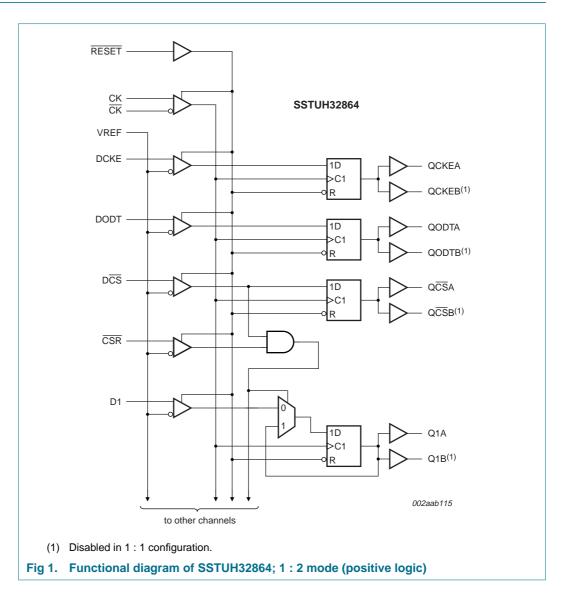
Table 1:Ordering information

 $T_{amb} = 0 \circ C$ to $+70 \circ C$.

Type number	Solder process	Package		
		Name	Description	Version
SSTUH32864EC/G	Pb-free (SnAgCu solder ball compound)	LFBGA96	plastic low profile fine-pitch ball grid array package; 96 balls; body $13.5 \times 5.5 \times 1.05$ mm	SOT536-1
SSTUH32864EC	SnPb solder ball compound	LFBGA96	plastic low profile fine-pitch ball grid array package; 96 balls; body $13.5 \times 5.5 \times 1.05$ mm	SOT536-1



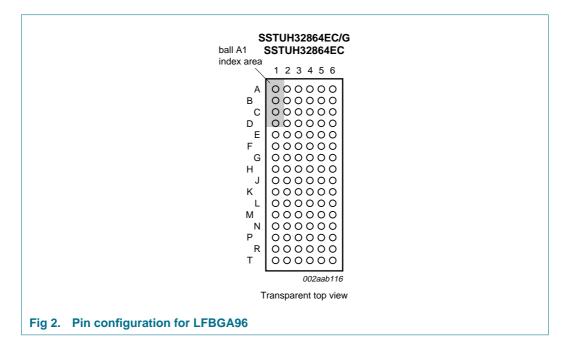
4. Functional diagram





5. Pinning information

5.1 Pinning



	1	2	3	4	5	6
А	DCKE	n.c.	VREF	V_{DD}	QCKE	DNU
В	D2	D15	GND	GND	Q2	Q15
С	D3	D16	V _{DD}	V _{DD}	Q3	Q16
D	DODT	n.c.	GND	GND	QODT	DNU
Е	D5	D17	V _{DD}	V _{DD}	Q5	Q17
F	D6	D18	GND	GND	Q6	Q18
G	n.c.	RESET	V _{DD}	V _{DD}	C1	C0
н	СК	DCS	GND	GND	QCS	DNU
J	СК	CSR	V _{DD}	V _{DD}	ZOH	ZOL
К	D8	D19	GND	GND	Q8	Q19
L	D9	D20	V _{DD}	V _{DD}	Q9	Q20
М	D10	D21	GND	GND	Q10	Q21
N	D11	D22	V _{DD}	V _{DD}	Q11	Q22
Р	D12	D23	GND	GND	Q12	Q23
R	D13	D24	V _{DD}	V _{DD}	Q13	Q24
Т	D14	D25	VREF	V _{DD}	Q14	Q25
						002aaa

Fig 3. Ball mapping; 1:1 register (C0 = 0, C1 = 0); top view

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	1	2	3	4	5	6
А	DCKE	n.c.	VREF	V _{DD}	QCKEA	QCKEB
В	D2	DNU	GND	GND	Q2A	Q2B
С	D3	DNU	V _{DD}	V _{DD}	Q3A	Q3B
D	DODT	n.c.	GND	GND	QODTA	QODTB
E	D5	DNU	V _{DD}	V _{DD}	Q5A	Q5B
F	D6	DNU	GND	GND	Q6A	Q6B
G	n.c.	RESET	V _{DD}	V _{DD}	C1	C0
н	СК	DCS	GND	GND	QCSA	QCSB
J	СК	CSR	V _{DD}	V _{DD}	ZOH	ZOL
К	D8	DNU	GND	GND	Q8A	Q8B
L	D9	DNU	V _{DD}	V _{DD}	Q9A	Q9B
М	D10	DNU	GND	GND	Q10A	Q10B
Ν	D11	DNU	V _{DD}	V _{DD}	Q11A	Q11B
Р	D12	DNU	GND	GND	Q12A	Q12B
R	D13	DNU	V _{DD}	V _{DD}	Q13A	Q13B
т	D14	DNU	VREF	V _{DD}	Q14A	Q14B
						002aaa950

Fig 4. Ball mapping; 1 : 2 register A (C0 = 0, C1 = 1); top view

	1	2	3	4	5	6				
А	D1	n.c.	VREF	V _{DD}	Q1A	Q1B				
В	D2	DNU	GND	GND	Q2A	Q2B				
С	D3	DNU	V _{DD}	V _{DD}	Q3A	Q3B				
D	D4	n.c.	GND	GND	Q4A	Q4B				
Е	D5	DNU	V _{DD}	V _{DD}	Q5A	Q5B				
F	D6	DNU	GND	GND	Q6A	Q6B				
G	n.c.	RESET	V _{DD}	V _{DD}	C1	C0				
н	СК	DCS	GND	GND	QCSA	QCSB				
J	CK	CSR	V _{DD}	V _{DD}	ZOH	ZOL				
К	D8	DNU	GND	GND	Q8A	Q8B				
L	D9	DNU	V _{DD}	V _{DD}	Q9A	Q9B				
М	D10	DNU	GND	GND	Q10A	Q10B				
Ν	DODT	DNU	V _{DD}	V _{DD}	QODTA	QODTB				
Ρ	D12	DNU	GND	GND	Q12A	Q12B				
R	D13	DNU	V _{DD}	V _{DD}	Q13A	Q13B				
т	DCKE	DNU	VREF	V _{DD}	QCKEA	QCKEB				
		002aaa95								

Fig 5. Ball mapping; 1 : 2 register B (C0 = 1, C1 = 1); top view

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5.2 Pin description

Table 2: Pin d	escription		
Symbol	Pin	Туре	Description
GND	B3, B4, D3, D4, F3, F4, H3, H4, K3, K4, M3, M4, P3, P4	ground input	ground
V _{DD}	A4, C3, C4, E3, E4, G3, G4, J3, J4, L3, L4, N3, N4, R3, R4, T4	1.8 V nominal	power supply voltage
VREF	A3, T3	0.9 V nominal	input reference voltage
ZOH	J5	input	reserved for future use
ZOL	J6	input	reserved for future use
СК	H1	differential input	positive master clock input
CK	J1	differential input	negative master clock input
C0, C1	G6, G5	LVCMOS inputs	configuration control inputs
RESET	G2	LVCMOS input	Asynchronous reset input (active LOW). Resets registers and disables VREF data and clock differential-input receivers.
$\overline{\text{CSR}}, \overline{\text{DCS}}$	J2, H2	SSTL_18 input	Chip select inputs (active LOW). Disables data outputs switching when both inputs are HIGH ^[2] .
D1 to D25	<u>[1]</u>	SSTL_18 input	Data inputs. Clocked in on the crossing of the rising edge of CK and the falling edge of \overline{CK} .
DODT	<u>[1]</u>	SSTL_18 input	The outputs of this register will not be suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control.
DCKE	<u>[1]</u>	SSTL_18 input	The outputs of this register will not be suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control.
Q1 to Q25, Q1A to Q14A, Q1B to Q14B	[1]	1.8 V CMOS	The outputs that are suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control [3].
Q CS , Q CS A, Q CS B	<u>[1]</u>	1.8 V CMOS	data outputs that will not be suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control
QODT, QODTA, QODTB	<u>[1]</u>	1.8 V CMOS	data outputs that will not be suspended by $\overline{\text{DCS}}$ and $\overline{\text{CSR}}$ control
QCKE, QCKEA, QCKEB	<u>[1]</u>	1.8 V CMOS	data outputs that will not be suspended by $D\overline{CS}$ and \overline{CSR} control
n.c.	A2, D2, G1	-	Not connected. Ball present but no internal connection to the die.
DNU	<u>[1]</u>	-	Do-not-use. Ball internally connected to the die which should be left open-circuit.

[1] Depends on configuration. See Figure 3, Figure 4, and Figure 5 for ball number.

[2] Configurations: Data inputs = D2, D3, D5, D6, D8 to D25 when C0 = 0 and C1 = 0. Data inputs = D2, D3, D5, D6, D8 to D14 when C0 = 0 and C1 = 1. Data inputs = D1 to D6, D8 to D10, D12, D13 when C0 = 1 and C1 = 1.
[3] Configurations:

Data outputs = Q2, Q3, Q5, Q6, Q8 to Q25 when C0 = 0 and C1 = 0. Data outputs = Q2, Q3, Q5, Q6, Q8 to Q14 when C0 = 0 and C1 = 1. Data outputs = Q1 to Q6, Q8 to Q10, Q12, Q13 when C0 = 1 and C1 = 1.

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6. Functional description

6.1 Function table

Table 3: Function table (each flip-flop)

L = LOW voltage level; *H* = HIGH voltage level; *X* = don't care; \uparrow = LOW-to-HIGH transition; \downarrow = HIGH-to-LOW transition

		Inp	uts				Outputs [1	1
RESET	DCS	CSR	СК	CK	Dn, DODT, DCKE	Qn	QCS	QODT, QCKE
Н	L	L	\uparrow	\downarrow	L	L	L	L
Н	L	L	\uparrow	\downarrow	Н	Н	L	Н
Н	L	L	L or H	L or H	Х	Q ₀	Q_0	Q_0
Н	L	Н	\uparrow	\downarrow	L	L	L	L
Н	L	Н	\uparrow	\downarrow	Н	Н	L	Н
Н	L	Н	L or H	L or H	Х	Q ₀	Q ₀	Q ₀
Н	Н	L	\uparrow	\downarrow	L	L	Н	L
Н	Н	L	\uparrow	\downarrow	Н	Н	Н	Н
Н	Н	L	L or H	L or H	Х	Q ₀	Q_0	Q ₀
Н	Н	Н	\uparrow	\downarrow	L	Q ₀	Н	L
Н	Н	Н	\uparrow	\downarrow	Н	Q ₀	Н	Н
Н	Н	Н	L or H	L or H	Х	Q ₀	Q_0	Q ₀
L	X or floating	L	L	L				

[1] Q_0 is the previous state of the associated output.

7. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DD}	supply voltage		-0.5	+2.5	V
VI	receiver input voltage		-0.5 <u>[1]</u>	+2.5 [2]	V
Vo	driver output voltage		-0.5[1]	V _{DD} + 0.5 ^[2]	V
I _{IK}	input clamp current	$V_I < 0 V \text{ or } V_I > V_{DD}$	-	±50	mA
I _{OK}	output clamp current	$V_O < 0 V \text{ or } V_O > V_{DD}$	-	±50	mA
lo	continuous output current	$0 V < V_O < V_{DD}$	-	±50	mA
I _{CCC}	continuous current through each V _{DD} or GND pin		-	±100	mA
T _{stg}	storage temperature		-65	+150	°C

[1] The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

[2] This value is limited to 2.5 V maximum.

8. Recommended operating conditions

Table 5:	Operating conditions						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DD}	supply voltage			1.7	-	1.9	V
V _{ref}	reference voltage			$0.49 \times V_{DD}$	$0.50 \times V_{\text{DD}}$	$0.51 \times V_{\text{DD}}$	V
V _{TT}	termination voltage			$V_{\text{ref}} - 0.040$	V _{ref}	V _{ref} + 0.040	V
VI	input voltage			0	-	V _{DD}	V
V _{IH(AC)}	AC HIGH-level input voltage	data inputs (Dn), CSR		V _{ref} + 0.250	-	-	V
V _{IL(AC)}	AC LOW-level input voltage	data inputs (Dn), CSR		-	-	$V_{ref} - 0.250$	V
V _{IH(DC)}	DC HIGH-level input voltage	data inputs (Dn), CSR		V _{ref} + 0.125	-	-	V
V _{IL(DC)}	DC LOW-level input voltage	data inputs (Dn), CSR		-	-	$V_{ref} - 0.125$	V
V _{IH}	HIGH-level input voltage	RESET, Cn	<u>[1]</u>	$0.65 \times V_{DD}$	-	V _{DD}	V
V _{IL}	LOW-level input voltage	RESET, Cn	<u>[1]</u>	-	-	$0.35 \times V_{\text{DD}}$	V
V _{ICR}	common mode input voltage range	CK, CK	[2]	0.675	-	1.125	V
V _{ID}	differential input voltage	CK, CK	[2]	600	-	-	mV
I _{OH}	HIGH-level output current			-	-	–12	mA
I _{OL}	LOW-level output current			-	-	12	mA
T _{amb}	ambient temperature	operating in free air		0	-	+70	°C

[1] The RESET and Cn inputs of the device must be held at valid logic levels (not floating) to ensure proper device operation.

[2] The differential inputs must not be floating, unless RESET is LOW.



9. Characteristics

Table 6: Characteristics

Recommended operating conditions; $T_{amb} = 0 \circ C$ to +70 $\circ C$; voltages are referenced to GND (ground = 0 V); unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{он}	HIGH-level output voltage	I _{OH} = –12 mA; V _{DD} = 1.7 V	1.2	-	-	V
V _{OL}	LOW-level output voltage	I_{OL} = 12 mA; V_{DD} = 1.7 V	-	-	0.5	V
I	input current	all inputs; V _I = V _{DD} or GND; V _{DD} = 1.9 V	-5	-	+5	μA
I _{DD}	static standby current	$\overline{\text{RESET}}$ = GND; I _O = 0 mA; V _{DD} = 1.9 V	-	-	100	μA
	static operating current	$\label{eq:response} \begin{split} \overline{RESET} &= V_{DD}; \ I_{O} = 0 \ mA; \\ V_{DD} &= 1.9 \ V; \\ V_{I} &= V_{IH(AC)} \ or \ V_{IL(AC)} \end{split}$	-	-	40	mA
			-	16	-	μΑ
	dynamic operating current per MHz, per each data input, 1 : 1 mode	$\label{eq:RESET} \begin{split} \overline{RESET} &= V_{DD};\\ \overline{V}_{I} &= V_{IH(AC)} \text{ or } V_{IL(AC)}; CK \text{ and}\\ \overline{CK} \text{ switching at 50 \% duty}\\ \text{cycle. One data input switching}\\ \text{at half clock frequency, 50 \%}\\ \text{duty cycle. I}_{O} &= 0 \text{ mA};\\ \overline{V}_{DD} &= 1.9 V \end{split}$	-	11	-	μΑ
	dynamic operating current per MHz, per each data input, 1 : 2 mode	$\label{eq:RESET} \begin{split} & RESET = V_{DD}; \\ & V_I = V_{IH(AC)} \text{ or } V_{IL(AC)}; CK \text{ and} \\ & \overline{CK} \text{ switching at 50 \% duty} \\ & cycle. \text{ One data input switching} \\ & at half clock frequency, 50 \% \\ & duty cycle. \ I_O = 0 \text{ mA}; \\ & V_DD = 1.9 V \end{split}$	-	19	-	μΑ
Ci	input capacitance, data inputs, CSR	V_{I} = V_{ref} \pm 250 mV; V_{DD} = 1.8 V	2.5	-	3.5	pF
	input capacitance, CK and \overline{CK}	$V_{ICR} = 0.9 \text{ V}; V_{ID} = 600 \text{ mV};$ $V_{DD} = 1.8 \text{ V}$	2	-	3	pF
	input capacitance, RESET	$V_{I} = V_{DD}$ or GND; $V_{DD} = 1.8$ V	2	-	4	pF

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Table 7: Timing requirements

Recommended operating conditions; $T_{amb} = 0 \degree C$ to +70 $\degree C$; $V_{DD} = 1.8 V \pm 0.1 V$; unless otherwise specified. See Figure 6 through Figure 11.

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
f _{clock}	clock frequency			-	-	450	MHz
t _W	pulse duration, CK, CK HIGH or LOW			1	-	-	ns
t _{ACT}	differential inputs active time		[1] [2]	-	-	10	ns
t _{INACT}	differential inputs inactive time		<u>[1] [3]</u>	-	-	15	ns
t _{su}	setup time	$\frac{D\overline{CS}}{CSR} \text{ before } CK \uparrow, \overline{CK} \downarrow, \\\overline{CSR} \text{ HIGH}$		0.7	-	-	ns
		$\frac{D\overline{CS}}{CSR} \text{ before } CK \uparrow, \overline{CK} \downarrow,$		0.5	-	-	ns
		$\overline{\text{CSR}}$, DODT, DCKE, and data before CK \uparrow , $\overline{\text{CK}}\downarrow$		0.5	-	-	ns
t _h	hold time	D \overline{CS} , \overline{CSR} , DODT, DCKE, and data after CK 1, $\overline{CK} \downarrow$		0.5	-	-	ns

[1] This parameter is not necessarily production tested.

[2] Data inputs must be active below a minimum time of $t_{ACT(max)}$ after \overline{RESET} is taken HIGH.

[3] Data and clock inputs must be held at valid levels (not floating) a minimum time of t_{INACT(max)} after RESET is taken LOW.

Table 8: Switching characteristics

Recommended operating conditions; $T_{amb} = 0 \circ C$ to +70 $\circ C$; $V_{DD} = 1.8 V \pm 0.1 V$;

Class I, $V_{ref} = V_{TT} = V_{DD} \times 0.5$ and $C_L = 10 \text{ pF}$; unless otherwise specified. See <u>Figure 6</u> through <u>Figure 11</u>.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f _{MAX}	maximum input clock frequency		450	-	-	MHz
t _{PDM}	propagation delay	CK and \overline{CK} to output	^[1] 1.41	-	1.8	ns
t _{PDMSS}	propagation delay, simultaneous switching	CK and \overline{CK} to output	[1][2] _	-	2.0	ns
t _{PHL}	propagation delay	RESET to output	-	-	3	ns

[1] Includes 350 ps of test-load transmission line delay.

[2] This parameter is not necessarily production tested.

Table 9:Output edge rates

Recommended operating conditions, unless otherwise specified. V_{DD} = 1.8 V \pm 0.1 V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV/dt_r	rising edge slew rate		1	-	4	V/ns
dV/dt_f	falling edge slew rate		1	-	4	V/ns
dV/dt_ Δ	absolute difference between dV/dt_r and dV/dt_f		-	-	1	V/ns

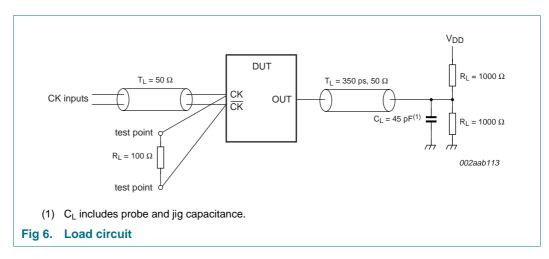
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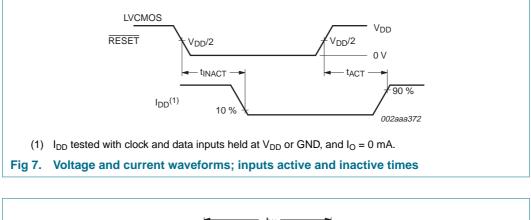
10. Test information

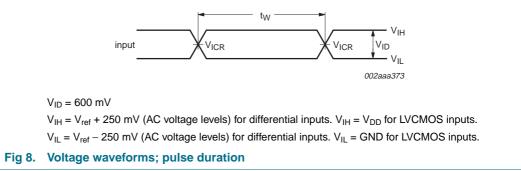
10.1 Test circuit

All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; Z₀ = 50 Ω ; input slew rate = 1 V/ns ± 20 %, unless otherwise specified.

The outputs are measured one at a time with one transition per measurement.

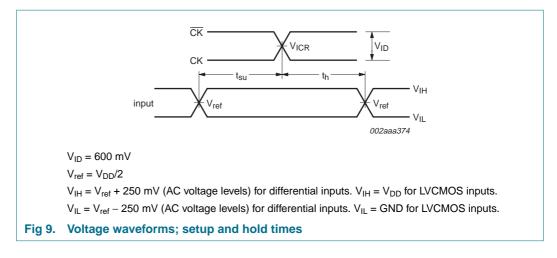


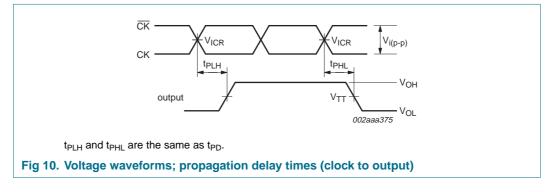


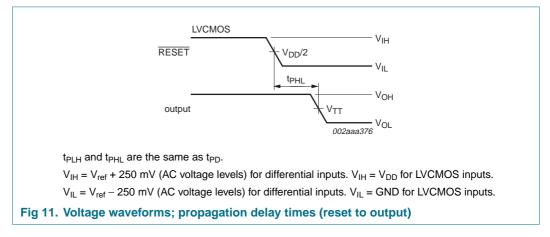


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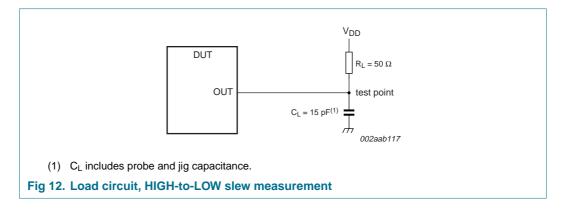


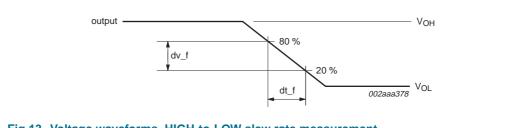
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10.2 Output slew rate measurement

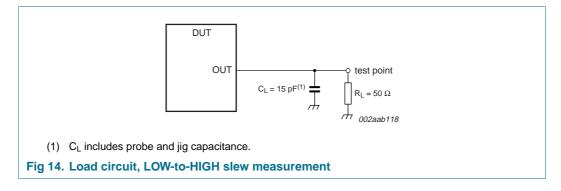
 V_{DD} = 1.8 V \pm 0.1 V.

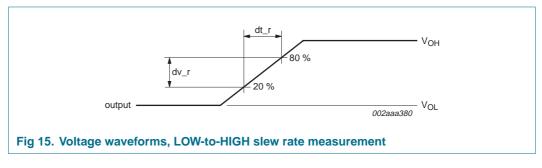
All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; Z₀ = 50 Ω ; input slew rate = 1 V/ns \pm 20 %, unless otherwise specified.







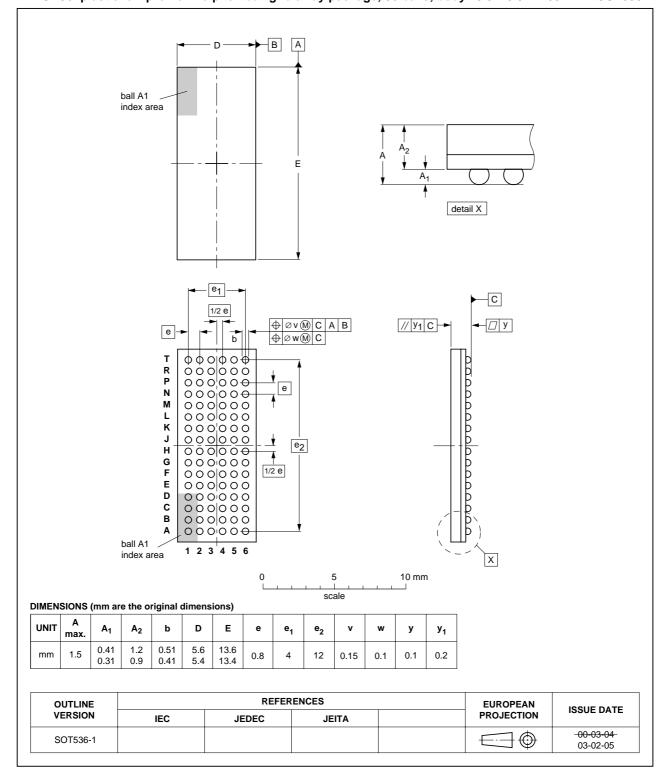




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11. Package outline



LFBGA96: plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 x 5.5 x 1.05 mm SOT536-1

Fig 16. Package outline SOT536-1 (LFBGA96)



12. Soldering

12.1 Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *Data Handbook IC26; Integrated Circuit Packages* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

12.2 Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Driven by legislation and environmental forces the worldwide use of lead-free solder pastes is increasing.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 seconds and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 °C to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferably be kept:

- below 225 °C (SnPb process) or below 245 °C (Pb-free process)
 - for all BGA, HTSSON..T and SSOP..T packages
 - for packages with a thickness \geq 2.5 mm
 - for packages with a thickness < 2.5 mm and a volume ≥ 350 mm³ so called thick/large packages.
- below 240 °C (SnPb process) or below 260 °C (Pb-free process) for packages with a thickness < 2.5 mm and a volume < 350 mm³ so called small/thin packages.

Moisture sensitivity precautions, as indicated on packing, must be respected at all times.

12.3 Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;

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- smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time of the leads in the wave ranges from 3 seconds to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

12.4 Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 $^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 seconds to 5 seconds between 270 $^{\circ}$ C and 320 $^{\circ}$ C.

12.5 Package related soldering information

Table 10:	Suitability of surface mount IC	packages for wave and reflow soldering methods

Package [1]	Soldering method	
	Wave	Reflow ^[2]
BGA, HTSSONT ^[3] , LBGA, LFBGA, SQFP, SSOPT ^[3] , TFBGA, VFBGA, XSON	not suitable	suitable
DHVQFN, HBCC, HBGA, HLQFP, HSO, HSOP, HSQFP, HSSON, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ^[4]	suitable
PLCC ^[5] , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended [5] [6]	suitable
SSOP, TSSOP, VSO, VSSOP	not recommended [7]	suitable
CWQCCNL ^[8] , PMFP ^[9] , WQCCNL ^[8]	not suitable	not suitable

 For more detailed information on the BGA packages refer to the (LF)BGA Application Note (AN01026); order a copy from your Philips Semiconductors sales office.

- [2] All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods.
- [3] These transparent plastic packages are extremely sensitive to reflow soldering conditions and must on no account be processed through more than one soldering cycle or subjected to infrared reflow soldering with peak temperature exceeding 217 °C ± 10 °C measured in the atmosphere of the reflow oven. The package body peak temperature must be kept as low as possible.

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- [4] These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- [5] If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- [6] Wave soldering is suitable for LQFP, QFP and TQFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- [7] Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.
- [8] Image sensor packages in principle should not be soldered. They are mounted in sockets or delivered pre-mounted on flex foil. However, the image sensor package can be mounted by the client on a flex foil by using a hot bar soldering process. The appropriate soldering profile can be provided on request.
- [9] Hot bar soldering or manual soldering is suitable for PMFP packages.

13. Abbreviations

Table 11:	Abbreviations	
Acronym	Description	
CMOS	Complementary Metal Oxide Silicon	
DDR	Double Data Rate	
DIMM	Dual In-line Memory Module	
LFBGA	Low profile Fine-pitch Ball Grid Array	
LVCMOS	Low Voltage Complementary Metal Oxide Silicon	
PRR	Pulse Repetition Rate	
RDIMM	Registered Dual In-line Memory Module	
SSTL	Stub Series Terminated Logic	

14. Revision history

Table 12: Revision history					
Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
SSTUH32864_1	20050422	Product data sheet	-	9397 750 14137	-

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15. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Date of release: 22 April 2005 Document number: 9397 750 14137

